1. Record Nr. UNISA996385700203316

Autore	B. H
Titolo	True but sad and dolefull nevves from Shrevvesbvry [[electronic resource]] : expressed in two several letters : whereof the one was written to a gentleman of the inner-temple : the other to a friend in London relating at large the severall passages of the late skirmish at or near Worcester between a party of each army, viz : under the command of Prince Robert on the one side and of Colonell Sands on the other : confirmed by a letter sent from Prince Robert to His Maiestie, Septemb. 24 with divers other circumstances of severall passages at that time : with cornents mottoes Octob. 10, 1642
Pubbl/distr/stampa	London, : [s.n.], 1642
Descrizione fisica	8 p
Altri autori (Persone)	Rupert, Prince, Count Palatine, <1619-1682.>
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Originally Published : Yorke, 1642. "Sad and dolefull newes from Shrewsbvry" signed: B.H. "A true copy of a letter sent by Prince Robert [i.e. Rupert] to His Majestie ..." p. 7. Reproduction of original in Thomason Collection, British Library.
Sommario/riassunto	eebo-0158

2. Record Nr. UNINA9911006694703321

Autore	Gao Jianjun <1968->
Titolo	RF and microwave modeling and measurement techniques for field effect transistors / / Jianjun Gao
Pubbl/distr/stampa	Raleigh, NC, : SciTech Pub., c2010
ISBN	1-61353-090-0 1-61344-286-6
Descrizione fisica	1 online resource (351 p.)
Disciplina	621.3815/284
Soggetti	Field-effect transistors - Testing Compound semiconductors - Testing Field-effect transistors - Mathematical models Compound semiconductors - Mathematical models Microwave measurements Radio measurements
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Contents; Preface; Chapter 1 - Introduction; Chapter 2 - Representation of Microwave Two-Port Network; Chapter 3 - Microwave and RF Measurement Techniques; Chapter 4 - FET Small Signal Modeling and ParameterExtraction; Chapter 5 - FET Nonlinear Modeling and ParameterExtraction; Chapter 6 - Microwave Noise Modeling and ParameterExtraction Technique for FETs; Chapter 7 - Artificial Neural Network Modeling Techniquefor FET; References; Index
Sommario/riassunto	This book is an introduction to microwave and RF signal modeling and measurement techniques for field effect transistors. It assumes only a basic course in electronic circuits and prerequisite knowledge for readers to apply the techniques and improve the performance of integrated circuits, reduce design cycles and increase their chance at first time success. The first chapters offer a general overview and discussion of microwave signal and noise matrices, and microwave measurement techniques. The following chapters address modeling techniques for field effect transistors and cover models such